L	Hits	Search Text	DB	Time stamp
Number	77.0	((470/701) (470/702) (470/702)	/ICPAT	2001/01/05
13	3381	((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
		or (438/305) or (438/306) or (438/307) or	US-PGPUB	13:50
		(438/920)).CCLS.	LICPAT	
14	743	LDMOS or "lateral double diffused metal oxide	USPAT;	2004/04/15
		semiconductor" or "lateral double-diffused metal oxide	US-PGPUB	13:51
		semiconductor or		
		"lateral-double-diffused-metal-oxide-semiconductor"	/ICBAT	
15	1416	RSD or "reduced surface drain" or	USPAT;	2004/04/15
,		"reduced-surface-drain"	US-PGPUB	13:51
16	9	(LDMOS or "lateral double diffused metal oxide	USPAT;	2004/04/15
		semiconductor" or "lateral double-diffused metal oxide	US-PGPUB	13:51
		semiconductor or	•	
		"lateral-double-diffused-metal-oxide-semiconductor")		
		and (RSD or "reduced surface drain" or		
		"reduced-surface-drain")		
17	1	(((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
		or (438/305) or (438/306) or (438/307) or	US-PGPUB	13:51
		(438/920)).CCLS.) and ((LDMOS or "lateral		
		double diffused metal oxide semiconductor" or "lateral		
		double-diffused metal oxide semiconductor" or		
		"lateral-double-diffused-metal-oxide-semiconductor")		
		and (RSD or "reduced surface drain" or		
		"reduced-surface-drain"))		
18	9	(((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
		or (438/305) or (438/306) or (438/307) or	US-PGPUB	13:55
		(438/920)).CCLS.) and (RSD or "reduced surface		
		drain" or "reduced-surface-drain")		
19	34	(((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
		or (438/305) or (438/306) or (438/307) or	US-PGPUB	13:55
		(438/920)).CCLS.) and (LDMOS or "lateral double		
		diffused metal oxide semiconductor" or "lateral		
		double-diffused metal oxide semiconductor" or		
		"lateral-double-diffused-metal-oxide-semiconductor")		
20	3404420	@ad<20010821	USPAT;	2004/04/15
			US-PGPUB	13:56
21	2.8	((((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
		or (438/305) or (438/306) or (438/307) or	US-PGPUB	14:05
		(438/920)).CCLS.) and (LDMOS or "lateral double		
		diffused metal oxide semiconductor" or "lateral		
		double-diffused metal oxide semiconductor" or		
		"lateral-double-diffused-metal-oxide-semiconductor"))		
		and @ad<20010821		
23	1160	(implant or implants or implanted or implanting or	USPAT;	2004/04/15
		implantation) with (heat or heats or heated or heating or	US-PGPUB	14:08
		anneal or anneals or annealed or annealing) with		
		((dielectric or dielctrics or insulating or insulatings or		
		oxide or oxides) with (gate or gates))		

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24	204	(((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
		or (438/305) or (438/306) or (438/307) or	US-PGPUB	14:09
		(438/920)).CCLS.) and ((implant or implants or	0.0 . 0.0	
		implanted or implanting or implantation) with (heat or		
		heats or heated or heating or anneal or anneals or		
		annealed or annealing) with ((dielectric or dieletrics or		
		insulating or insulatings or oxide or oxides) with (gate or		
		gates)))		
25	1	(((((438/301) or (438/302) or (438/303) or (438/304)	USPAT;	2004/04/15
2)	'	or (438/305) or (438/306) or (438/307) or	US-PGPUB	14:10
		1	40-10140	17:10
		(438/920)).CCLS.) and (LDMOS or "lateral double		
		diffused metal oxide semiconductor" or "lateral		
		double-diffused metal oxide semiconductor" or		
		"lateral-double-diffused-metal-oxide-semiconductor"))		
		and @ad<20010821) and ((((438/301) or (438/302) or		
		(438/303) or (438/304) or (438/305) or (438/306) or		
		(438/307) or (438/920)).CCLS.) and ((implant or		
		implants or implanted or implanting or implantation) with		
		(heat or heats or heated or heating or anneal or anneals		
		or annealed or annealing) with ((dielectric or dieletrics or		
		insulating or insulatings or oxide or oxides) with (gate or		•
		gates))))		
26	911	((implant or implants or implanted or implanting or	USPAT;	2004/04/15
	-	implantation) with (heat or heats or heated or heating or	US-PGPUB	14:11
		anneal or anneals or annealed or annealing) with		
		((dielectric or dieletrics or insulating or insulatings or		
		oxide or oxides) with (gate or gates))) and		
		@ad<20010821		
27	9	(RSD or "reduced surface drain" or	USPAT;	2004/04/15
		"reduced-surface-drain") and ((LDMOS or "lateral	US-PGPUB	14:11
		double diffused metal oxide semiconductor" or "lateral		
		double-diffused metal oxide semiconductor" or		
		"lateral-double-diffused-metal-oxide-semiconductor")		
		and (RSD or "reduced surface drain" or		
		"reduced-surface-drain"))		
2.8	0	(((implant or implants or implanted or implanting or	USPAT;	2004/04/15
		implantation) with (heat or heats or heated or heating or	US-PGPUB	14:11
		anneal or anneals or annealed or annealing) with		
		((dielectric or dielectrics or insulating or insulatings or		
		oxide or oxides) with (gate or gates))) and		
		@ad<20010821) and ((RSD or "reduced surface drain"		
		or "reduced-surface-drain") and ((LDMOS or "lateral		
		double diffused metal oxide semiconductor" or "lateral		
		double-diffused metal oxide semiconductor" or		
		"lateral-double-diffused-metal-oxide-semiconductor")		
		and (RSD or "reduced surface drain" or		
		"reduced-surface-drain")))		
		reduced-surrace-drain")))	L	1

29	173	@ad<20010821 and ((((438/301) or (438/302) or	USPAT;	2004/04/15
		(438/303) or (438/304) or (438/305) or (438/306) or	US-PGPUB	14:12
		(438/307) or (438/920)).CCLS.) and ((implant or		
		implants or implanted or implanting or implantation) with		
		(heat or heats or heated or heating or anneal or anneals		
		or annealed or annealing) with ((dielectric or dieletrics or		
		insulating or insulatings or oxide or oxides) with (gate or		
		gates))))		